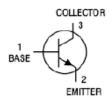


MMBT5087

PNP Silicon Epitaxial Planar Transistors

for switching and AF amplifier applications





Marking: 2Q SOT-23

Absolute Maximum Ratings (Ta = 25 oC)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	50	V
Collector Emitter Voltage	-V _{CEO}	45	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	50	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at $T_a = 25 \text{ oC}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at -V _{CE} = 5 V, -I _C = 1 mA Current Gain Group	h _{FE}	150	400	- - -
Collector Base Cutoff Current at -V _{CB} = 50 V	-I _{CBO}	-	50	nA
Emitter Base Cutoff Current at -V _{EB} = 5 V	-I _{EBO}	-	50	nA
Collector Base Breakdown Voltage at -I _C = 100 μA	-V _{(BR)CBO}	50	-	V
Collector Emitter Breakdown Voltage at -I _C = 1 mA	-V _{(BR)CEO}	45	-	V
Emitter Base Breakdown Voltage at -I _E = 100 μA	-V _{(BR)EBO}	5	-	V
Collector Emitter Saturation Voltage at -I _C = 100 mA, -I _B = 5 mA	-V _{CE(sat)}	-	0.65	V
Base Emitter Saturation Voltage at -I _C = 100 mA, -I _B = 5 mA	-V _{BE(sat)}	-	1	V
Gain Bandwidth Product at -V _{CE} = 5 V, -I _C = 10 mA	f _T	100	-	MHz
Output Capacitance at -V _{CB} = 10 V, f = 1 MHz	Сов	-	7	pF
Noise Figure at -V _{CE} = 5 V, -I _C = 200 μ A, f = 1 KHz, R _G = 2 K Ω	NF	-	10	dB

SHIKE MAKE CONSCIOUS PRODUCT

Conscious Products Begin With Conscious People





MMBT5087

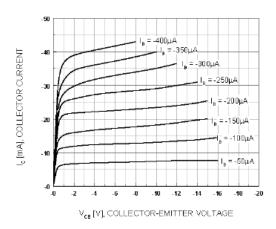


Figure 1. Static Characteristic

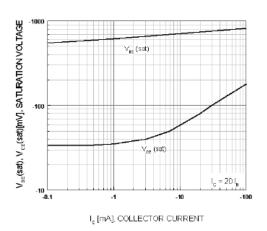


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

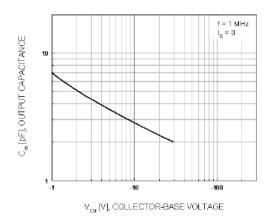
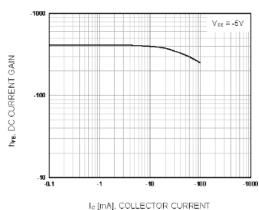


Figure 5. Collector Output Capacitance



IE [IIIA], COLLECTOR CORRENT

Figure 2. DC current Gain

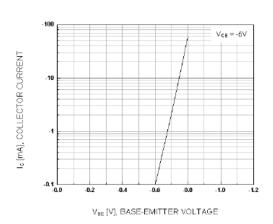


Figure 4. Base-Emitter On Voltage

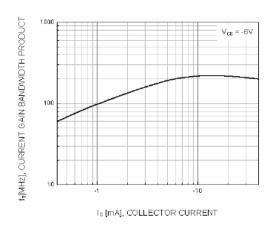


Figure 6. Current Gian Bandwidth Product

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